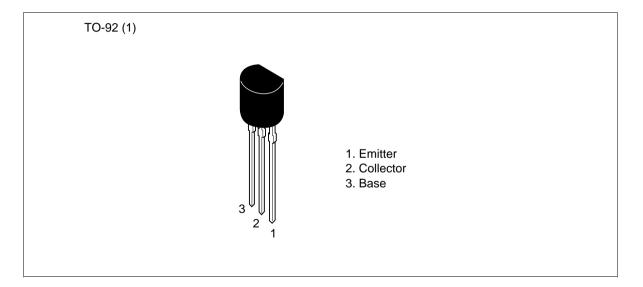
Silicon PNP Epitaxial

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Application

Low frequency amplifier

Outline



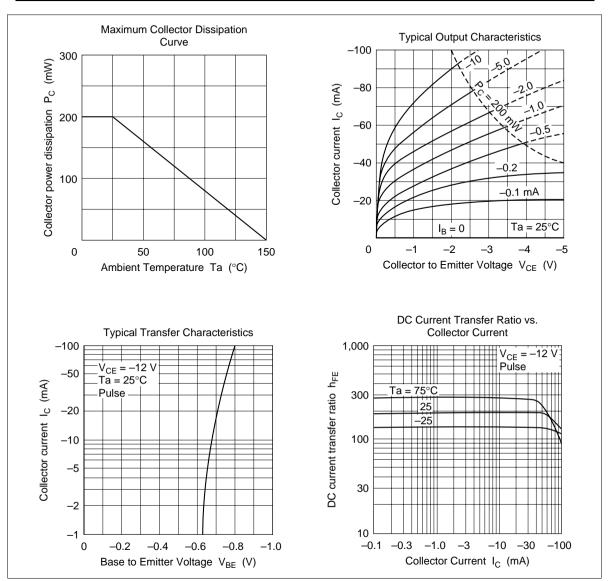


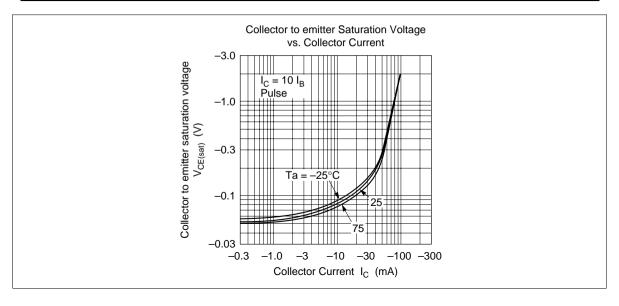
Absolute Maximum Ratings ($Ta = 25^{\circ}C$)

Item	Symbol	Ratings	Unit
Collector to base voltage	V _{CBO}	-200	V
Collector to emitter voltage	V _{CEO}	-200	V
Emitter to base voltage	V _{EBO}	-5	V
Collector current	Ι _c	-100	mA
Collector power dissipation	Pc	200	mW
Junction temperature	Tj	150	°C
Storage temperature	Tstg	-55 to +150	°C

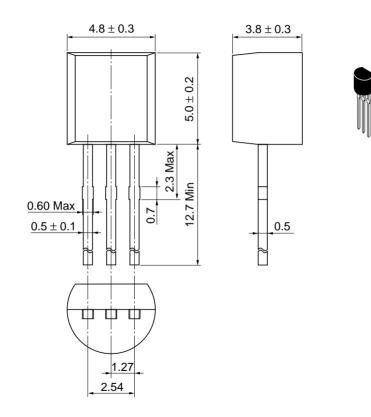
Electrical Characteristics ($Ta = 25^{\circ}C$)

Item	Symbol	Min	Тур	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{\rm (BR)CBO}$	-200	_	_	V	$I_{c} = -10 \ \mu A, \ I_{E} = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	-200	—	—	V	$I_{\rm C}$ = -0.5 mA, $R_{\rm BE}$ = ∞
Emitter to base breakdown voltage	$V_{(\text{BR})\text{EBO}}$	-5	—		V	$I_{\rm E} = -10 \ \mu A, \ I_{\rm C} = 0$
Collector cutoff current	I _{CEO}	_	_	-500	μΑ	V_{CE} = -200 V, R_{BE} = ∞
DC current transfer ratio	h _{FE}	100	_	250		$V_{ce} = -12 \text{ V}, \text{ I}_{c} = -2 \text{ mA}^{*1}$
Collector to emitter saturation voltage	$V_{\text{CE(sat)}}$	—	_	-0.5	V	$I_{c} = -30 \text{ mA}, I_{B} = -3 \text{ mA}^{*1}$
Base to emitter voltage	V _{BE}	—	_	-1.0	V	$V_{ce} = -12 \text{ V}, \text{ I}_{c} = -2 \text{ mA}^{*1}$
Note: 1. Pulse test						





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Hitachi Code	TO-92 (1)
JEDEC	Conforms
EIAJ	Conforms
Weight (reference value)	0.25 g

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Semiconductor & Integrated Circuits. Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan Tel: Tokyo (03) 3270-2111 Fax: (03) 3270-5109 NorthAmerica URL http:semiconductor.hitachi.com/ http://www.hitachi-eu.com/hel/ecg Europe http://www.has.hitachi.com.sg/grp3/sicd/index.htm http://www.hitachi.com.tw/E/Product/SICD_Frame.htm Asia (Singapore) Asia (Taiwan) Asia (HongKong) http://www.hitachi.com.hk/eng/bo/grp3/index.htm http://www.hitachi.co.jp/Sicd/indx.htm Japan For further information write to: Hitachi Semiconductor Hitachi Europe GmbH Hitachi Asia Pte. Ltd. (America) Inc. Electronic components Group 16 Collyer Quay #20-00 179 East Tasman Drive, Dornacher Stra§e 3 Hitachi Tower San Jose,CA 95134 D-85622 Feldkirchen, Munich Singapore 049318 Tel: <1> (408) 433-1990 Fax: <1>(408) 433-0223 Germany Tel: 535-2100 Tel: <49> (89) 9 9180-0 Fax: 535-1533 Fax: <49> (89) 9 29 30 00

 Fax: <49> (89) 9 29 30 00
 Hita

 Hitachi Europe Ltd.
 Hita

 Electronic Components Group.
 Taip

 Whitebrook Park
 3F,

 Lower Cookham Road
 Tun

 Maidenhead
 Tel:

 Berkshire SL6 8YA, United Kingdom
 Fax

 Tel: <44> (1628) 585000

 Fax: <44> (1628) 778322

Hitachi Asia Ltd. Taipei Branch Office 3F, Hung Kuo Building. No.167, Tun-Hwa North Road, Taipei (105) Tel: <886> (2) 2718-3666 Fax: <886> (2) 2718-8180

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Hitachi Asia (Hong Kong) Ltd. Group III (Electronic Components) 7/F., North Tower, World Finance Centre, Harbour City, Canton Road, Tsim Sha Tsui, Kowloon, Hong Kong Tel: <852> (2) 735 9218 Fax: <852> (2) 730 0281 Telex: 40815 HITEC HX

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